

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claim 1 (Currently Amended): A method for manufacturing a semiconductor device equipped with a capacitor in which a dielectric film is used, wherein a complex oxide is used as a mask material when the dielectric film is ~~[etched]~~ subjected to reactive ion etching, and the mask material, which is in direct contact with the dielectric film, is used as an upper electrode of the capacitor after the reactive ion etching is performed.

Claim 2 (Original): The method according to claim 1, wherein the complex oxide contains SrRuO_3 as a main component.

Claim 3 (Currently Amended): The method according to claim 1, wherein the complex oxide is a conductive oxide, ~~and the mask material is used as an electrode of the capacitor or part of the electrode after the etching.~~

Claim 4 (Canceled).

Claim 5 (Original): The method according to claim 1, wherein the dielectric film contains PZT as a main component.

Claim 6 (Currently Amended): The method according to claim 1, wherein Pt, Ir, Ru, IrO_2 , RuO_2 , or a laminated structure or a mixture of them is used as a material of ~~[an]~~ a lower electrode of the capacitor.

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Claim 7 (Original): A semiconductor device equipped with a capacitor in which a dielectric film is used, wherein a mask material used in etching the dielectric film is prepared as an electrode of the capacitor.

Claim 8 (Original): The semiconductor device according to claim 7, wherein the dielectric film is a ferroelectric film.

Claim 9 (Original): The device according to claim 8, wherein the ferroelectric film is PZT.

Claim 10 (Original): The device according to claim 7, wherein Pt, Ir, Ru, IrO₂, RuO₂, or a laminated structure or a mixture of them is used as a material of the electrode of the capacitor.